Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of the Claims:

1-14. (cancelled)

15. (currently amended) A method for manufacturing a semiconductor device; comprising:

providing a substrate that includes a first principal surface and a second principal surface opposite the first principal surface;

placing semiconductor elements on the first principal surface;

placing the substrate on an insulating region of a lower die;

pressing an upper die ~~in which~~ having multiple shape-forming parts ~~are formed~~ lined with a polymer film against the lower die ~~through the medium of a polymer film~~, the polymer film contacting a first conductive region on the first principal surface; and

supplying a liquid resin for molding the semiconductor elements.

16. (original) The manufacturing method of Claim 15, wherein the lower die includes a ceramic member, and the second principal surface of the substrate is mounted on the ceramic member.

17. (original) The manufacturing method described in Claim 15, wherein the lower die includes an insulating film, and the second principal surface of the substrate is mounted on the insulating film.

18. (original) The manufacturing method described in Claim 15, wherein the insulating region is larger than the second principal surface of the substrate.

19. (original) The manufacturing method described in Claim 15, wherein the polymer film is held by suction in the multiple shape-forming parts by air intake from air intake holes formed in the upper die.

20. (currently amended) The manufacturing method described in Claim 15, wherein the ~~substrate includes a~~ first conductive region on the first principal surface~~, and the first conductive region~~ is electrically connected to semiconductor elements.

21. (currently amended) The semiconductor manufacturing device described in Claim [[21]] 20, wherein the first conductive region is uncovered by the molded resin.

22. (original) The manufacturing method described in Claim 15, wherein the substrate includes a second conductive region on the second principal surface, and the second conductive region is electrically connected to the first conductive region or semiconductor elements.

23. (currently amended) The manufacturing method described in ~~any one of Claims~~ claim 15, wherein the substrate is a multilayer circuit board.

24. (currently amended) The manufacturing method described in ~~any one of Claims~~ claim 15, further comprising a step of cutting the substrate into individual semiconductor elements.

25. (currently amended) The manufacturing method described in ~~any one of Claims~~ claim 20, further comprising a step of stacking terminals of a second semiconductor device onto the first conductive region on the first principal surface of the substrate.

26. (new) A method for manufacturing a semiconductor device; comprising:

providing a substrate that includes a first principal surface and a second principal surface opposite the first principal surface;

placing semiconductor elements on the first principal surface;

placing the substrate on a ceramic region enclosed by an o-ring in a lower die;

pressing an upper die against the o-ring; and

supplying a liquid resin for molding the semiconductor elements.

27. (new) The method of claim 26, further comprising covering a conductive land on the first principal surface with the upper die.

28. (new) The method of claim 27, further comprising insulating the conductive land from the upper die with a insulative film.

29. (new) The method of claim 26, in which the lower die comprises a conductive material having a thermal expansion coefficient of the same order of the thermal expansion coefficient of the ceramic.